

Amendments to the Specification

Please amend the following paragraphs of the specification:

[0006] Turning now to FIGS. 5-9, a method or process flow is described for forming low capacitance region 10. As part of the embodiment described, trench isolation 34 and device region 31 also are described to show the integration of the present invention into an integrated circuit process flow. FIG. 5 shows a partial cross-sectional view of device 33 at an early stage of fabrication. For example, a first dielectric layer 41 is formed over a major surface of semiconductor region 30. By way of example, semiconductor region 30 comprises P-type silicon having a dopant concentration of about  $1.25 \times 10^{16}$  atoms/cm<sup>3</sup>. This dopant concentration is adjusted according to specific device specifications. Semiconductor region 30 comprises, for example, an epitaxial layer formed over a semiconductor substrate or region 36.